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Modeling of mechanical stress in silicon isolation technology and its influence on device ...

HA Rueda - 1999 - swamp.tec.ufl.edu

... the resistivities of the **semiconductor**. The energy band shifts are also influenced ...

compressive **stress** on pn-junction **device** current. This ...

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Micro-Raman spectroscopy to study local mechanical stress in silicon integrated circuits

I De Wolf - Semicond. Sci. Technol, 1996 - iop.org

... local mechanical **stress** in silicon integrated circuits ... Local mechanical **stress** is

currently an important topic of concern in microelectronics processing. ...

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ONLINE PUBLICATIONS

O Properties, GEJNS Sariciftci, SACST Lee, J Kido - Chem. Phys. Lett, 2001 - mrs.org

... be used as a through-space nano-contact to a **semiconductor** sample. ... a high brightness

of 3370 cd/m . The desirable **properties** of this **device** were attributed ...

[View as HTML](#) - [Web Search](#) - [lucy.mrs.org](#)

Strain-driven self-organization of nanostructures on semiconductor surfaces

VA Shchukin, D Bimberg - Appl. Phys. A, 1998 - springerlink.com

... object both for basic research and **device** applications. ... tum dots are used as an active

medium of **semiconductor** ... values of the intrinsic surface **stress** tensor τ ...

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In-Situ Stress State Measurements During Chip-on-Board Assembly

Y Zou, JC Suhling, RW Johnson, RC Jaeger, AKM Mian - IEEE Trans. Electron. Packag. Manufact, 1999 - ieeexplore.ieee.org

... 6512, a Hewlett Packard 4156 **semiconductor** parameter analyzer ... et al.: IN-SITU STRESS

STATE MEASUREMENTS 49 ... Temperature dependent mechanical **properties** and large ...

[Cited by 9](#) - [Web Search](#) - [ieeexplore.ieee.org](#)

Electrical properties and recombination activity of copper, nickel and cobalt in silicon

AA Istratov, ER Weber - Appl. Phys. A, 1998 - springerlink.com

... are the most common impurities in silicon **device** fabrication. ... of the importance of

iron for **semiconductor** in- dustry ... The **stress** can partly be relaxed, forming ...

[Cited by 34](#) - [Web Search](#) - [adsabs.harvard.edu](#)

Transport properties of Hg Zn x Se and Hg Mn x Se doped with Fe resonant donors

W Dobrowolski, RR Galazka, E Grodzicka, J Kossut, ... - Phys Rev B, 1993 - link.aps.org

... is expected to lead to a better **device** perfor- mance ... of the conduction band in a

narrow-gap **semiconductor**. ... Let us **stress** that in the latter samples doped only ...

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Superhard diamondlike carbon: preparation, theory, and properties

Q Wei, J Narayan - International Materials Reviews, 2000 - ingenta.com

... techniques of **fabrication**, theoretical modelling, ... frac- tion, density, and internal

stress are directly ... density, thermal conductivity, etc.) **properties** of the ...

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Properties of Glass Surfaces

Ernsberger... - Annual Review of Materials Science, 1972 - arjournals.annualreviews.org

... supports or interfaces with an- other material or **device** to form ... PROPERTIES OF GLASS

SURFACES ... interesting type of yield behavior when the **stress** conditions are ...

[Cited by 1](#) - [Web Search](#) - [arjournals.annualreviews.org](#)

Physical Properties of Multi-wall Nanotubes

L Forro, C Schonenberger - Carbon Nanotubes, 2000 - springerlink.com

... MWNTs, it is useful to briefly highlight the important electronic **properties** of

the ... electrons, a material can in general be either a metal or a **semiconductor**. ...

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1 [Special issue: AI in engineering](#)

D. Sriram, R. Joobbani

January 1985 **ACM SIGART Bulletin**, Issue 91
 Full text available: [pdf\(8.79 MB\)](#) Additional Information: [full citation](#), [abstract](#)

The papers in this special issue were compiled from responses to the announcement in the July 1984 issue of the SIGART newsletter and notices posted over the ARPAnet. The interest being shown in this area is reflected in the sixty papers received from over six countries. About half the papers were received over the computer network.

2 [RAID: high-performance, reliable secondary storage](#)

Peter M. Chen, Edward K. Lee, Garth A. Gibson, Randy H. Katz, David A. Patterson

June 1994 **ACM Computing Surveys (CSUR)**, Volume 26 Issue 2
 Full text available: [pdf\(3.60 MB\)](#) Additional Information: [full citation](#), [abstract](#), [references](#), [citations](#), [index terms](#), [review](#)

Disk arrays were proposed in the 1980s as a way to use parallelism between multiple disks to improve aggregate I/O performance. Today they appear in the product lines of most major computer manufacturers. This article gives a comprehensive overview of disk arrays and provides a framework in which to organize current and future work. First, the article introduces disk technology and reviews the driving forces that have popularized disk arrays: performance and reliability. It discusses the tw ...

Keywords: RAID, disk array, parallel I/O, redundancy, storage, striping

3 [Research directions in virtual environments: report of an NSF Invitational Workshop, March 23-24, 1992, University of North Carolina at Chapel Hill](#)

Gary Bishop, Henry Fuchs

August 1992 **ACM SIGGRAPH Computer Graphics**, Volume 26 Issue 3
 Full text available: [pdf\(2.33 MB\)](#) Additional Information: [full citation](#), [citations](#), [index terms](#)

4 Integrating computer technology, people technology and application technology: strategies and case studies from Georgia Tech's Graphics, Visualization and Usability Center

Jim Foley


June 1994 **Proceedings of the workshop on Advanced visual interfaces**

Full text available:  [pdf\(1.27 MB\)](#) Additional Information: [full citation](#), [index terms](#)

5 A unified approach to test data analysis

Michael A. Gianfagna

June 1978 **Proceedings of the 15th conference on Design automation**


Full text available:  [pdf\(581.18 KB\)](#) Additional Information: [full citation](#), [abstract](#), [references](#), [citations](#), [index terms](#)

To provide cost-effective performance evaluation or engineering feedback from circuit test results often requires that complex analyses be performed on large volumes of non-standard data. Using a large scale data management system and a modular design philosophy, a system to cope with the above requirements has been developed. TDAS (Test Data Analysis System) has provided timely and economic solutions to test data analysis problems which might have been intractable by other means.

6 Quo Vadimus: computer science in a decade

J. F. Traub

June 1981 **Communications of the ACM**, Volume 24 Issue 6

Full text available:  [pdf\(2.35 MB\)](#) Additional Information: [full citation](#), [abstract](#), [citations](#), [index terms](#)

A panel discussion was held during the third biennial meeting of chairmen of Ph.D.-granting computer science departments in June, 1978 at Snowbird, Utah, a meeting sponsored by the Computer Science Board. Invitees from industry and government were also present. A report was prepared from tapes made of the discussion (Department of Computer Science, Carnegie-Mellon University: Report #CMU-CS-80-127, June 1980). It contained all the prepared statements of the panelists, lightly edited, and th ...

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Micro-Raman spectroscopy to study local mechanical stress in silicon integrated circuits

I De Wolf - Semicond. Sci. Technol, 1996 - iop.org

... In the absence of stress, the corresponding three optical Raman modes of silicon have ... see section 2.4.) From a quantum physical point of view, Raman scattering ...

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Transport properties of Hg Zn x Se and Hg Mn x Se doped with Fe resonant donors

W Dobrowolski, RR Galazka, E Grodzicka, J Kossut, ... - Phys Rev B, 1993 - link.aps.org

... 17 848 1—" 1993 The American Physical Society TRANSPORT ... of the conduction band in a narrow-gap semiconductor. ... Let us stress that in the latter samples doped ...

[Web Search](#) - [adsabs.harvard.edu](#) - [ncbi.nlm.nih.gov](#)

Superhard diamondlike carbon: preparation, theory, and properties

Q Wei, J Narayan - International Materials Reviews, 2000 - ingenta.com

... sp3 frac- tion, density, and internal stress are directly ... physical (heat capacity, density, thermal conductivity, etc.) properties of the material. ...

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Properties of Glass Surfaces

Ernsberger... - Annual Review of Materials Science, 1972 - arjournals.annualreviews.org

... interfaces with an- other material or device to form ... These cleavages are instances of the physical reality (22 ... of yield behavior when the stress conditions are ...

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[P3] Ferroelectric thin films of PbTiO 3 on silicon

VR Palkar, SC Purandare, R Pinto - Journal of Physics D: Applied Physics, 1999 - iop.org

... proper charge compensation while the semiconductor cannot, making ... review of recent advances in physical vapour growth ... PbTiO 3 and their device applications by ...

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VW Antonetti - Physics Letters, 1973 - research.ibm.com

... Describing Carrier Distributions in Semiconductor Devices, M ... Method of Charge-Coupled Device Transfer Analysis ... Impact and Contact Stress Analysis in Multilayer ...

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Report to the American Physical Society by the study group on research planning for coal utilization ...

BR Cooper, WR Gruner, L Anderson, RH Davis, P ... - Reviews of Modern Physics, 1981 - link.aps.org

... We especially stress that coal researches by physicists can ... 1 ar gel, an amorpho us semiconductor, a conglomerate ... Physical techniques, such as low angle x-ray ...

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HIGH-PRESSURE SYNTHESIS, CHARACTERIZATION, AND TUNING OF SOLID STATE MATERIALS

JV Badding... - Annual Review of Materials Science, 1998 - matsci.annualreviews.org

... kinetics, the effect of nonhydrostatic stress, and the ... that mimics the effect of physical pressure. ... role in understanding bulk semiconductor band structures ...

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... Palo Alto, CA), Geo- physical Prospecting 28 ... and A. M. Tuxford (Na- tional Semiconductor Corporation, Santa ... Residual Stress, Chemical Etch Rate, Refractive Index ...

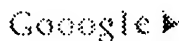
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NS Abakarova, O Ibragimov Kh, KM Aliev, IK Kamilov ... - Semicond. Sci. Technol, 2001 - ingenta.com

... in-plane and in-depth properties of the ... growth for the manufacture of semiconductor heterostructure devices ... Weber ER: Gettering simulator: physical basis and ...

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... Auger recombination in long-wavelength quantum-well semiconductor lasers using hydrostatic pressure

M Silver, EP O'Reilly, AR Adams - IEEE J. Quantum Electron, 1997 - ieeexplore.ieee.org

... Future optimization of device performance is being hampered ... were performed on an InP- based buried heterostructure ... were then used to calculate the threshold ...

Cited by 8 - [Web Search](#) - ieeexplore.ieee.org

SiGeC Nanostructures: a new path to Silicon based optoelectronics

S PSI-LMN, G FORTH, I INFM-PD - Appl. Phys. Lett, 2001 - hphys.jku.at

... output from SiGe structures is based on the ... in cooperation with the Institute for Semiconductor Physics at ... strain calculations are required to calculate of the ...

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Modeling of mechanical stress in silicon isolation technology and its influence on device ...

HA Rueda - 1999 - swamp.tec.ufl.edu

... DRAM) and complementary metal oxide semiconductor (CMOS) ... are generated will degrade device performance [5, 6 ... attainable pitch lengths of LOCOS-based technologies ...

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Industrial And Environmental Fluid Mechanics

JCR Hunt... - Annual Review of Fluid Mechanics, 1991 - fluid.annualreviews.org

... The second step was to make a 1/10-scale model test to simulate the air ... The design was based on the earlier studies, and the earlier flow- pattern results were ...

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A review on the molecular dynamics simulation of machining at the atomic scale

R Komanduri, LM Raff - Proceedings of the Institution of Mechanical Engineers B, ..., 2001 - ingentaconnect.com

... centred cubic (bcc) and hexagonal close packed (hcp)], a semiconductor, a ceramic ... trajectories of atoms obtained from the MD simula- tion [based on equations (1 ...

Cited by 1 - [Web Search](#) - ingentaconnect.com - ingenta.com - csa.com

SYMPOSIUM AA

CBCX Pan, KESH Tuller, T Wood - Phys. Rev. Lett, 1998 - lucy.mrs.org

... are both crucial to the performance of the ... network, an in uence of hydrostatic pressure, arising upon ... INTERFACE REACTIONS IN LiNbO BASED OPTOELEC- TRONICS ...

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Point defects and dopant diffusion in silicon

PM Fahey, PB Griffin, JD Plummer - Reviews of Modern Physics, 1989 - link.aps.org

... Armigliato, R., D. Nobili, P. Ostojic, M. Servidori, and S. Solmi, 1977, in Semiconductor Silicon 1977, edited by HR Huff and E. Sirtl (Electrochemical Society ...

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Muonium states in semiconductors

BD Patterson... - Reviews of Modern Physics, 1988 - link.aps.org

... account for the hyperfine frequency of Mu in a semiconductor was the ... Successively more detailed simulations of the muon states followed, based principally on ...

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